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03500.015894 (35.C15894)

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	
	:	Examiner: S. A. Gebremariam
Takaharu KONDO, et al.)	
	:	Group Art Unit: 2811
Application No.: 09/982,845)	
	:	
Filed: October 22, 2001)	
	:	
For: SILICON-BASED FILM AND)	
PHOTOVOLTAIC ELEMENT	:	May 13, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

STATEMENT OF SUBSTANCE OF INTERVIEW

Sir:

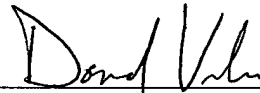
Applicants wish to thank the Examiner for the courtesies extended to Applicants' undersigned representative during the personal interview conducted on May 11, 2004.

During the interview, Claim 1 was discussed in view of U.S. Patent No. 6,211,454 (Sano '454). Applicants' representative argued that the range of spacing recited in Claim 1 is not inherent in Sano '454. In support of this argument, Applicants' representative directed the Examiner's attention to Comparative Example 1 of the present application, in which a silicon-based film formed on a substrate having a standard deviation of 20° has a spacing falling outside of the claimed range.

The Examiner indicated that the foregoing argument would be fully considered in the next Office communication. See Interview Summary dated May 11, 2004. Such action is courteously solicited.

Applicants' undersigned attorney may be reached in our Washington, D.C. office at (202) 530-1010. All correspondence should continue to be directed to our below-listed address.

Respectfully submitted,



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